



MBR1020FCT THRU MBR1060FCT

Schottky Diodes

Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guaranteed JESD22-B102

- Polarity: As marked

■Maximum Ratings (T_a=25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR1020FCT	MBR1035FCT	MBR1045FCT	MBR1050FCT	MBR1060FCT
Device marking code			MBR1020FCT	MBR1035FCT	MBR1045FCT	MBR1050FCT	MBR1060FCT
Repetitive Peak Reverse Voltage	VRRM	V	20	35	45	50	60
Average Rectified Output Current @60Hz sine wave, R-load, T _a =25	I _O	A	10				
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T _a =25	I _{FSM}	A	100				
Current Squared Time @1ms≤t<8.3ms T _j =25	I ² t	A ² s	41				
Storage Temperature	T _{stg}		-55 ~ +150				
Junction Temperature	T _j		-55 ~ +125			-55 ~ +150	

■Electrical Characteristics T_a=25 °C Unless otherwise specified

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR1020FCT	MBR1035FCT	MBR1045FCT	MBR1050FCT	MBR1060FCT
Maximum instantaneous forward voltage drop per diode	V _{FM}	V	I _{FM} =5.0A	0.55			0.75	
Maximum DC reverse current	I _{RRM1}	mA	V _{RM} =V _{RRM} T _a =25	0.2				
			V _{RM} =V _{RRM} T _a =100	20 °				



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■ Thermal Characteristics $T_a=25$ Unless otherwise specified

PARAMETER		SYMBOL	UNIT	MBR1020FCT	MBR1035FCT	MBR1040FCT	MBR1050FCT	MBR1060FCT
Thermal Resistance	Between junction and case	$R_{\theta J-C}$	$^{\circ}W$					
				4.0				

■ Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QU
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■Outline Dimensions